

Silicon NPN Power Transistors

2SC2556 2SC2556A

DESCRIPTION

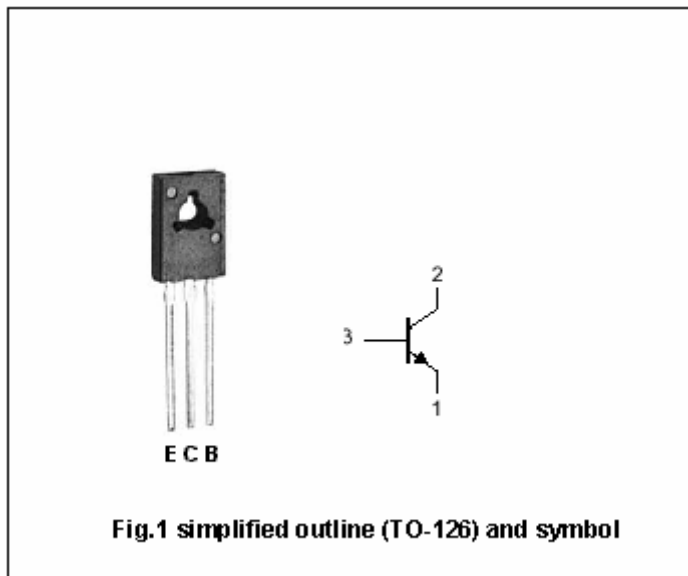
- With TO-126 package
- High V_{CBO}
- Low collector saturation voltage
- High transition frequency

APPLICATIONS

- Audio frequency output amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SC2556	130	V
		2SC2556A	180	
V_{CEO}	Collector- emitter voltage	2SC2556	40	V
		2SC2556A	50	
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1	A
I_{CM}	Collector current-peak		1.5	A
P_C	Collector power dissipation	$T_C=25^\circ C$	1.2	W
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature		-55°C+150	°C

Silicon NPN Power Transistors

2SC2556 2SC2556A

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SC2556	I _C =2mA ; I _B =0	40			V
		2SC2556A		50			
V _{(BR)CBO}	Collector-base breakdown voltage	2SC2556	I _C =10μA ; I _E =0	130			V
		2SC2556A		180			
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10μA ; I _C =0	5			V	
V _{CEsat}	Collector-emitter saturation voltage	I _C =500mA ; I _B =50mA			0.5	V	
I _{CBO}	Collector cut-off current	V _{CB} =120V ; I _E =0			0.1	μA	
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =0.5V	150		350		
h _{FE-2}	DC current gain	I _C =0.5A ; V _{CE} =2V	150				
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =20V ; f=1MHz			30	pF	
f _T	Transition frequency	I _C =50mA ; V _{CE} =10V		200		MHz	

Silicon NPN Power Transistors

2SC2556 2SC2556A

PACKAGE OUTLINE

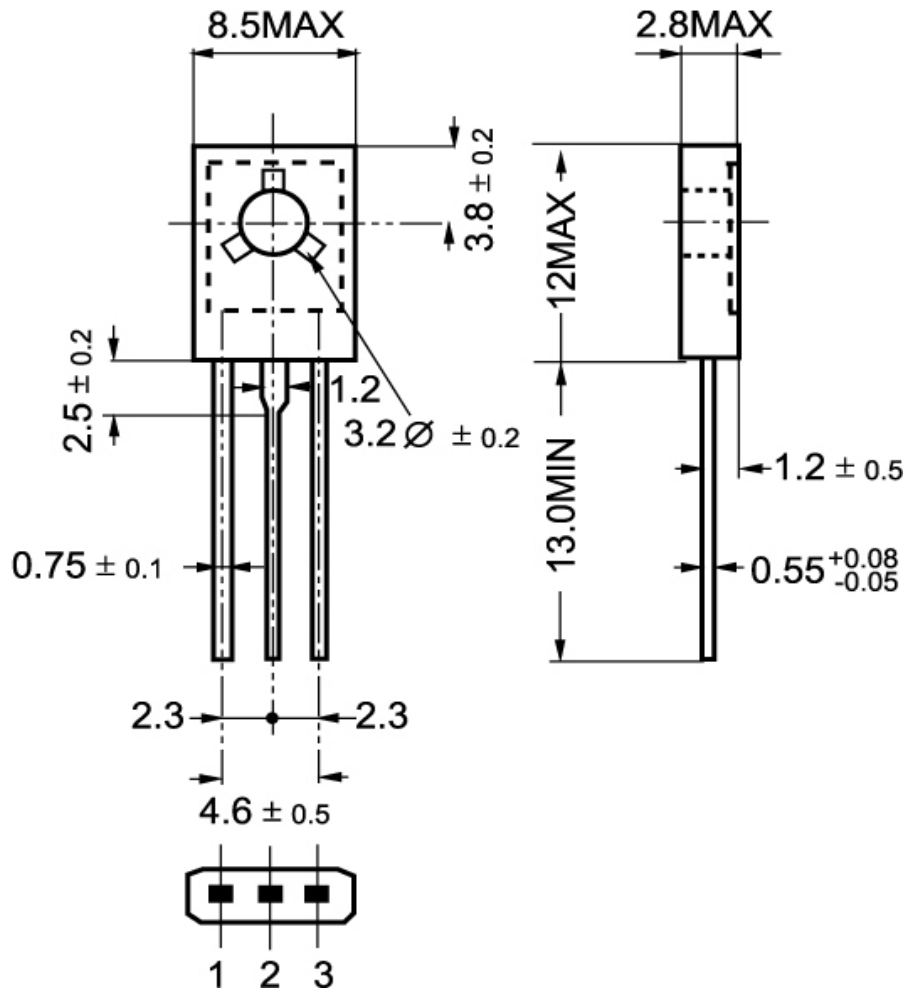


Fig.2 Outline dimensions